

<b>Notice of References Cited</b>	Application/Control No. 10/564,486		Applicant(s)/Patent Under Reexamination SON, HYO-KUN	
	Examiner Jesse Y. Miyoshi		Art Unit 2809	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,903,017 A	05-1999	Itaya et al.	257/190
*	B	US-6,285,696 B1	09-2001	Bour et al.	372/45.01
*	C	US-6,370,176 B1	04-2002	Okumura, Toshiyuki	372/45.01
*	D	US-6,586,762 B2	07-2003	Kozaki, Tokuya	257/14
*	E	US-6,711,191 B1	03-2004	Kozaki et al.	372/43.01
*	F	US-7,180,096 B2	02-2007	Wu et al.	257/79
*	G	US-7,193,246 B1	03-2007	Tanizawa et al.	257/94
*	H	US-6,337,493	01-2002	Tanizawa et al.	257/79
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP11220169	08-1999	Japan	Hisayoshi et al.	H01L 33/00
	O					
	P					
	Q					
	R					
	S					
	T					

#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Youn-Hoon KIM et al., Structural and Optical Properties of InGaN/GaN Multi-Quantum Well Structures with Different Well Widths, Spring 2003, Materials Research Society Symposium Proc. Vol. 722, K7.12.1
	V	Kenji Uchida, Photoluminescence Characteristics and Pit Formation of InGaN/GaN Quantum-Well Structures Grown on Sapphire Substrates by Low-Pressure Metalorganic Vapor Phase Epitaxy, March 1999, Journal of Electronic Materials
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.